

# RB551SS-30

## Silicon Epitaxial Planar Schottky Barrier Diode

### Features

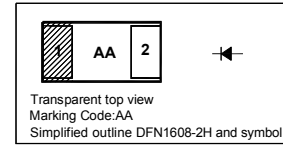
- High reliability
- Low leakage current

### Application

- General Rectification

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RM}$	30	V
Reverse Voltage	$V_R$	20	V
Average Rectified Forward Current	$I_{F(AV)}$	0.5	A
Peak Forward Surge Current (8.3 ms)	$I_{FSM}$	5	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

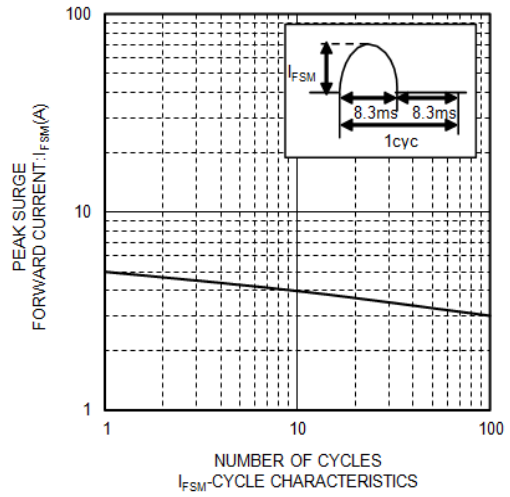
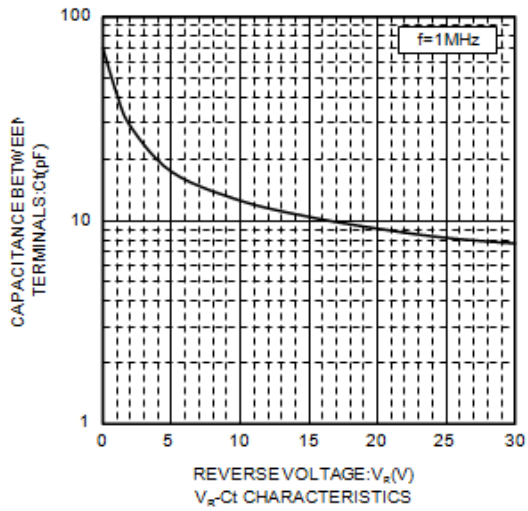
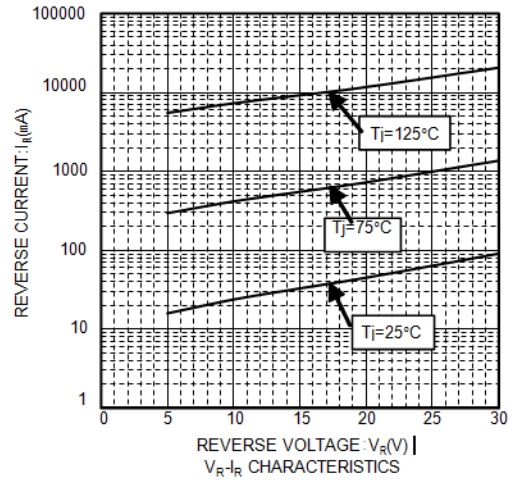
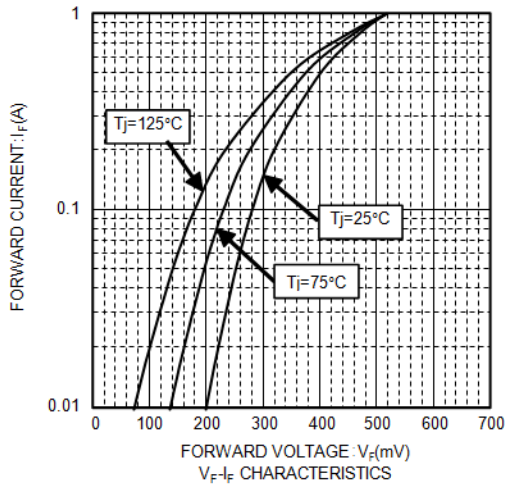
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 500\text{ mA}$	$V_F$	0.36 0.47	V
Reverse Current at $V_R = 20\text{ V}$	$I_R$	50	$\mu\text{A}$

**TOP DYNAMIC**



Dated: 12/02/2015 Rev: 01

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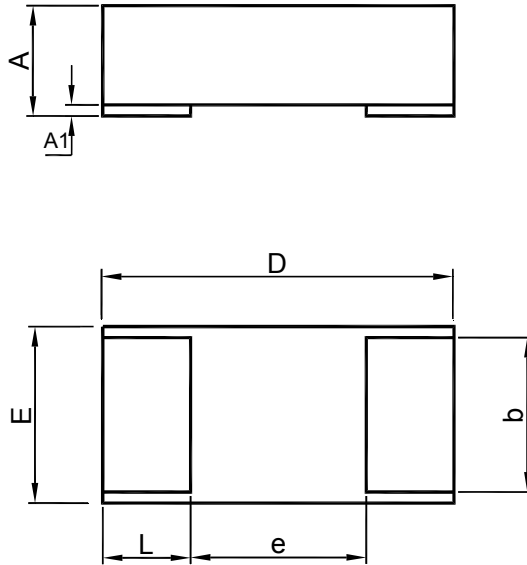


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## PACKAGE OUTLINE

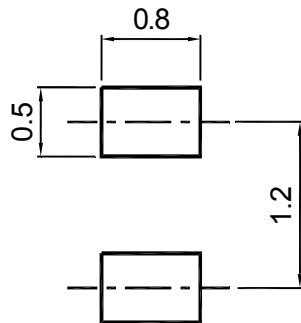
Plastic surface mounted package; 2 leads

DFN1608-2H



UNIT	A	A1	b	D	E	e	L
mm	0.55	0.05	0.75	1.65	0.85	0.85	0.45
	0.45	0	0.65	1.55	0.75	0.75	0.35

## RECOMMENDED SOLDERING FOOTPRINT



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1608	8	4 ± 0.1	0.157 ± 0.004	178	7	4,000

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